PTO/SB/17 (02-07)
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Effective on 12/08/2004. Spant to the Consolidated Appropriations Act, 2005 (H.R. 4818). Application Number EE TRANSMITTAL Filing Date First Named Inventor For FY 2007

Applicant claims small entity status. See 37 CFR 1.27

Complete If Known 10/533,147 April 27, 2005 MAEDA, et al. **Examiner Name** Seyed Masoud Malekzadeh Art Unit

TOTAL AMOUNT OF PAY	YMENT	(\$)180.00	All	omey Docket No.	1110/94	4198		
METHOD OF PAYMENT	T (check al	I that apply)	· · · · · · · · · · · · · · · · · · ·	· · · · · · · · · · · · · · · · · · ·				
Check Credit	Card	Money Order	None [Other (please	identify):			_
Deposit Account D	eposit Accou	nt Number: <u>23-0920</u>)	Deposit Accoun	t Name: Welsh	& Katz, Ltd.		_
For the above-ident	ified deposit	account, the Dire	ector is hereby a	authorized to: (che	k all that apply	y)		
	ditional fee(s) or underpayme	nts of fee(s)	Charge fee(s) Credit any ov		ow, except for the	filing fee	
under 37 CFR under 37 CFR WARNING: Information on thi information and authorization	s form may	become public. Cre	edit card informa	-	• •	form. Provide cred	it card	
FEE CALCULATION								
1. BASIC FILING, SEA	RCH, AND	EXAMINATIO	N FEES					
	FILING FEES		SEARCH	SEARCH FEES		ATION FEES		
		Small Entity		Small Entity		Small Entity		
Application Type	Fee (\$)	Fee (\$)	Fee (\$)	<u>Fee (\$)</u>	Fee (\$)	Fee (\$)	Fees Paid (\$)	
Utility	300	150	500	250	200	100		
Design	200	100	100	50	130	65 _		
Plant	200	100	300	150	160	80		
Reissue	300	150	500	250	600	300		
Provisional	200	100	0	0	0	0		
2. EXCESS CLAIM FEE	ES					<u>s</u>	mall Entity	
Fee Description						Fee (\$)	Fee (\$)	
Each claim over 20 (incl						50	25	
Each independent claim over 3 (including Reissues)					200	100		
Multiple dependent claims						360	180	
Total Claims - 20 or HP						Multiple Depe Fee (\$)	ndent Claims Fee Paid (\$)	
HP = highest number of total cla		if greater than 20				1 00 141	10010147	
Indep. Claims	Extra Ci		(\$) Fees P	aid (\$)				
- 3 or HP =	=	x	=					
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3. APPLICATION SIZE	FEE							
If the specification a	and drawir	igs exceed 100:	sheets of pape	er (excluding ele	ctronically fi	led sequence or	computer	
listings under 37 CF					or small entit	y) for each addi	tional 50	
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<u>Total Sheets</u> <u>Ex</u> - 100 =	tra Sheets	/50=		ditional 50 or frac		<u>Fee (\$)</u>	Fee Paid (\$)	
4. OTHER FEE(S)		_ ′30-		a up to a whole ha	11001) X		Fee Boid (\$)	
Non-English Specif	ication (\$130 fee (no am	all entity disc	count)			Fee Paid (\$)	
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SUBMITTED BY				
Signature	Covald T. Shiple	Registration No. 27.466 (Attorney/Agent)	Telephone	
Name (Print/Type	e) Gerald T. Shekleton		Date June 18, 2007	

This collection of information is required by 37 CFR 1.136. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 30 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re U.S. Patent Application

Applicant:

MAEDA et al.

Serial No.:

10/533,147

Filed:

April 26, 2005

For:

METHOD FOR PRODUCING SILICON WAFER

Art Unit: 1722

Confirmation

No.:

5289

I hereby certify that this correspondence is being deposited with the United Postal Service as first class mail in an envelope addressed to: Mailstop Amendment / Commissioner for Patents / PO Box 1450 / Alexandria, Virginia 22313-1450, on June 18, 2007.

Gerald T. Shekleton Reg.

No. 27,466

INFORMATION DISCLOSURE STATEMENT

Mail Stop AMENDMENT Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

Pursuant to 37 C.F.R. §1.97, a list of documents is disclosed on the attached Form PTO-1449 that may be material to the examination of this application.

No inferences should be drawn that the attached list represents a comprehensive investigation, or that any material disclosed is equivalent to the subject invention. In addition, none of the documents that have publication dates prior to the priority date of the above application anticipate the invention in this application.

The cited document(s) disclose numerous specific features. There has been no attempt to list each and every feature disclosed by each document. The Examiner is requested to review the

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Atty. Docket No. 94198

document(s) and determine the extent of the materiality of the document disclosures with respect to

the present invention.

The discussion of any art and the citation of any document(s) herein is not to be construed as an

admission that the art or document disclosure is necessarily within the invention field of endeavor,

that the art or document disclosure is necessarily prior in time to a particular date which may be

relevant to the instant patent application, and/or that the art or document disclosure is otherwise

necessarily prior art as defined by patent law with respect to the instant invention and application.

Also, there is observed the right to later set forth how the instant invention is distinguished over

the disclosure of any document or other art, including the disclosures of the art and document(s)

recited herein, that may be cited by the Examiner in rejecting a claim in the instant patent

application. The recitation herein of the art and document(s) is not to be construed as an assertion

that more pertinent art could not possibly be in existence.

Respectfully submitted,

WELSH & KATZ, LTD.

Gerald T. Shekleton

Registration No. 27,466

Date: <u>June</u> 18, 2007 WELSH & KATZ, LTD.

120 South Riverside Plaza

22nd Floor

Chicago, Illinois 60606-3913

· Telephone: 312/655-1500

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	US 6,565,822		Hoshi et al.									
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